

Type	Hits	Ref.	Search Text	DBs	Time Stamp
BRS	254	S15	analyzing near plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	3016	S17	(702/182 or 702/183 or 702/189 or 702/190).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	1497	S18	(118/723e).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	524	S19	(156/345.24 or 156/345.25).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	3573	S20	(216/59-61 or 216/67).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	8347	S21	S17 or S18 or S19 or S20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	4675	S22	S21 and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	210	S23	S22 and (RF near signal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	182	S24	S23 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	1	S16	S15 and ((RF or radio\$frequency)same ignite)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	85	S25	S24 and (etch near rate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	5	S26	S25 and (analyzing same plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	2	S27	S26 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	5	S28	S25 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	254	S29	analyzing near plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	3016	S31	(702/182 or 702/183 or 702/189 or 702/190).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	1497	S32	(118/723e).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	524	S33	(156/345.24 or 156/345.25).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	3573	S34	(216/59-61 or 216/67).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	8347	S35	S31 or S32 or S33 or S34	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	4675	S36	S35 and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	210	S37	S36 and (RF near signal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	182	S38	S37 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	254	S43	analyzing near plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	3016	S44	(702/182 or 702/183 or 702/189 or 702/190).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	1497	S45	(118/723e).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	524	S46	(156/345.24 or 156/345.25).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	3573	S47	(216/59-61 or 216/67).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	8347	S48	S44 or S45 or S46 or S47	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	4675	S49	S48 and plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	210	S50	S49 and (RF near signal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	182	S51	S50 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	1	S30	S29 and ((RF or radio\$frequency)same ignite)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	1	S52	S43 and ((RF or radio\$frequency)same ignite)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	85	S39	S38 and (etch near rate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	5	S40	S39 and (analyzing same plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	2	S41	S40 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	5	S42	S39 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	85	S53	S51 and (etch near rate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	5	S54	S53 and (analyzing same plasma)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	2	S55	S54 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06
BRS	5	S56	S53 and fourier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	02/02/06